BUK766R0-60E

N-channel TrenchMOS standard level FET

13 July 2012 Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	60	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 1	[1]	-	-	75	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	-	182	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		-	4.58	6	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 48 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	20	-	nC

[1] Continuous current is limited by package.

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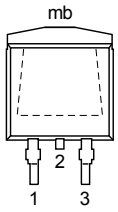
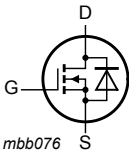
2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 D2PAK (SOT404)	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK766R0-60E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	60	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ		-	60	V
V_{GS}	gate-source voltage	T_j = 25 °C		-20	20	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; Fig. 1	[1]	-	75	A
		T_{mb} = 100 °C; V_{GS} = 10 V; Fig. 1	[1]	-	75	A
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs; Fig. 4		-	473	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	182	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	75	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	473	A

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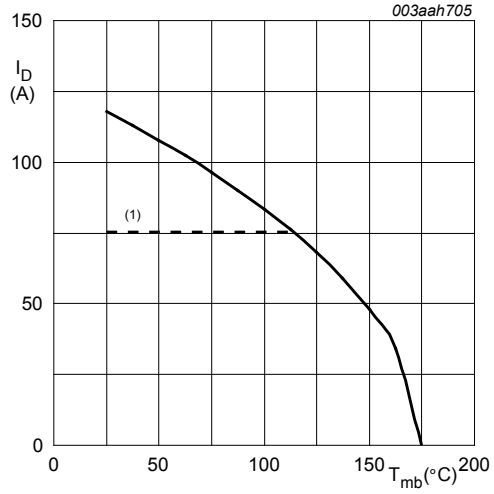
Symbol	Parameter	Conditions		Min	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \leq$ 60 V; R_{GS} = 50 Ω; V_{GS} = 60 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2][3]	-	196	mJ

[1] Continuous current is limited by package.
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
[3] Refer to application note AN10273 for further information.



(1) Capped at 75A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$V_{GS} \geq 10V$

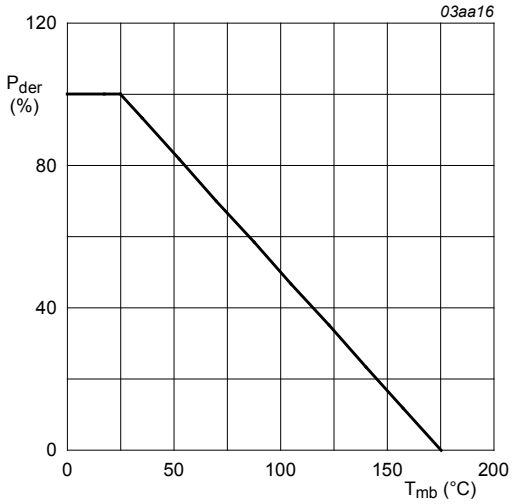


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

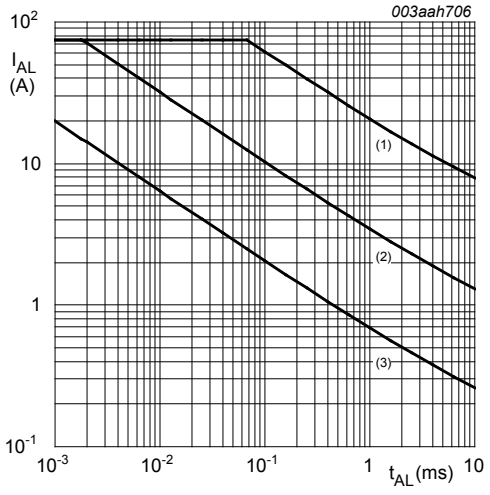


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 150°C$; (3) Repetitive Avalanche

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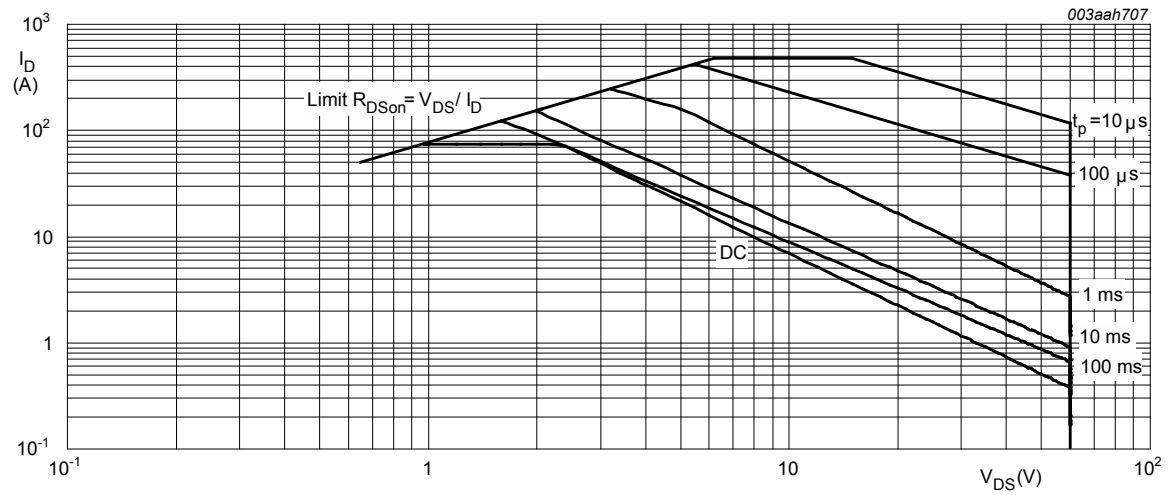

Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25°C$; I_{DM} *is a single pulse*

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	0.82	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board		-	50	-	K/W

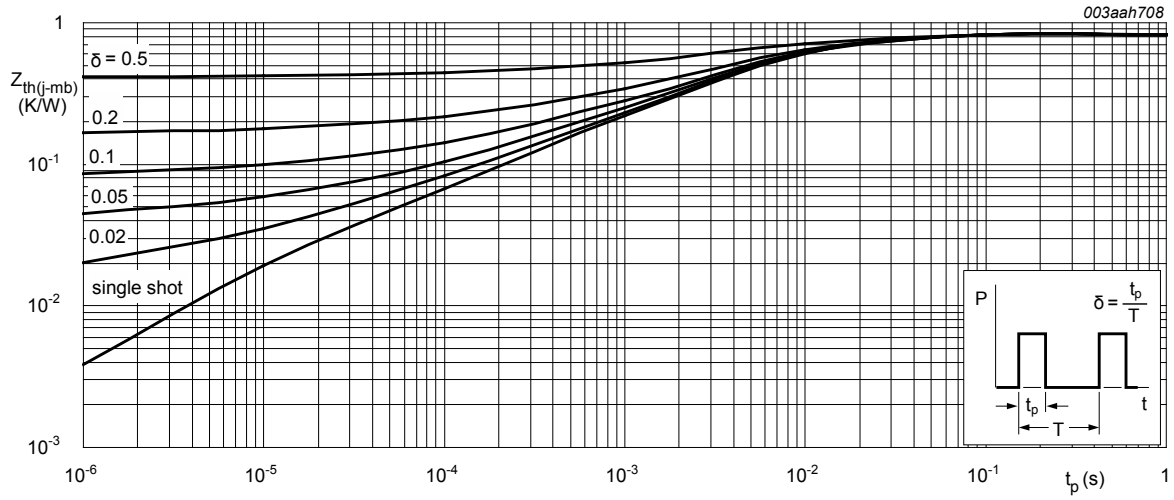

Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

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6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		60	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 9; Fig. 10		2.4	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 9		1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 9		-	-	4.5	V
I_{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C		-	0.05	1	µA
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		-	4.58	6	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 11; Fig. 12		-	-	13	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 48 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	62	-	nC
Q_{GS}	gate-source charge			-	16	-	nC
Q_{GD}	gate-drain charge			-	20	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	3390	4520	pF
C_{oss}	output capacitance			-	447	536	pF
C_{rss}	reverse transfer capacitance			-	272	372	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 45 V; R_L = 1.8 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω		-	19	-	ns
t_r	rise time			-	36	-	ns
$t_{d(off)}$	turn-off delay time			-	38	-	ns
t_f	fall time			-	34	-	ns
L_D	internal drain inductance	from upper edge of mounting base to centre of die		-	2.5	-	nH
L_S	internal source inductance	measured from source lead to source bond pad		-	7.5	-	nH

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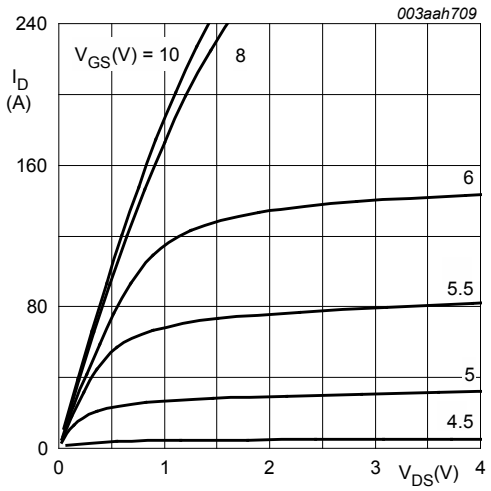
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.84	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V		-	35	-	ns
Q_r	recovered charge			-	43	-	nC



T_j = 25 °C; t_p = 300 µs

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

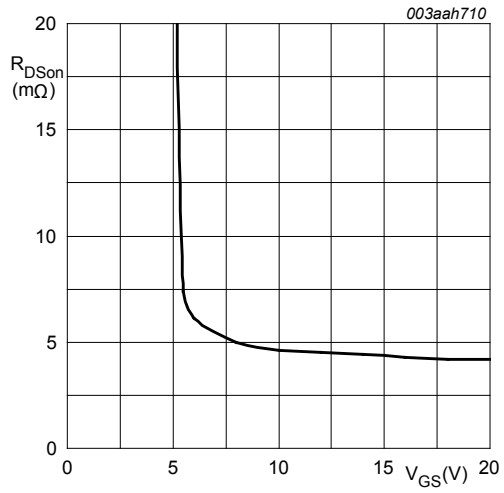


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25°C;\ I_D = 25A$

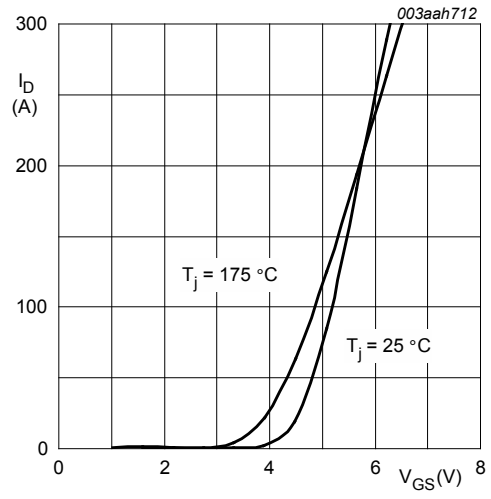


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

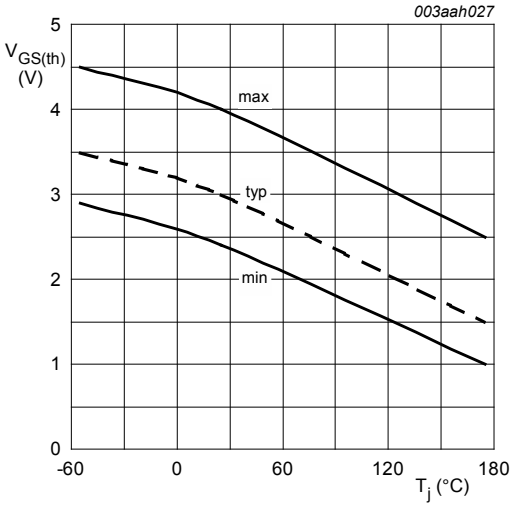


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\ \text{mA};\ V_{DS} = V_{GS}$

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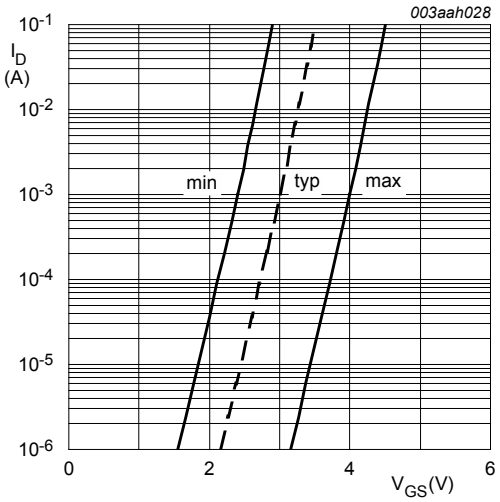
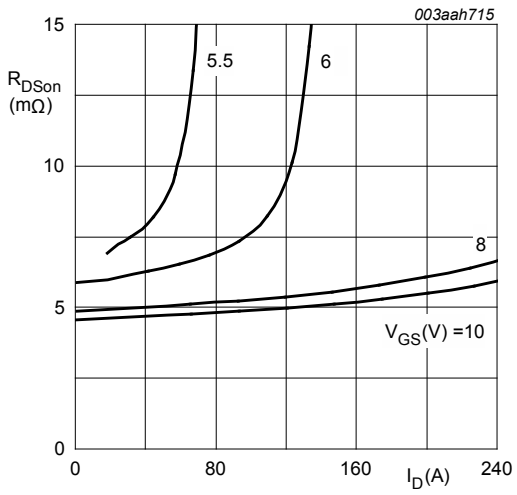


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C;\ V_{DS} = 5V$



T_j = 25 °C; t_p = 300 µs

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

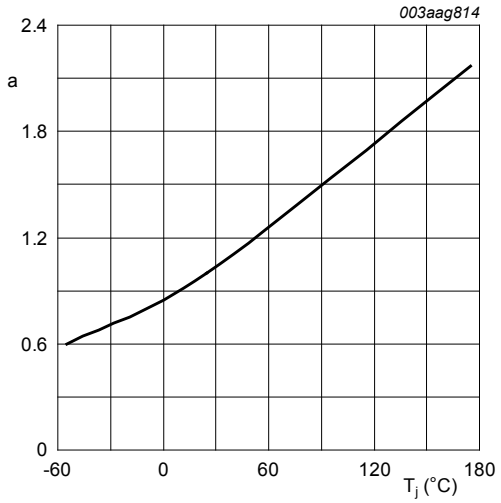


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$

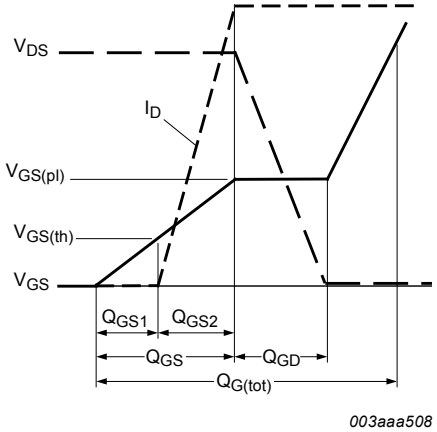


Fig. 13. Gate charge waveform definitions

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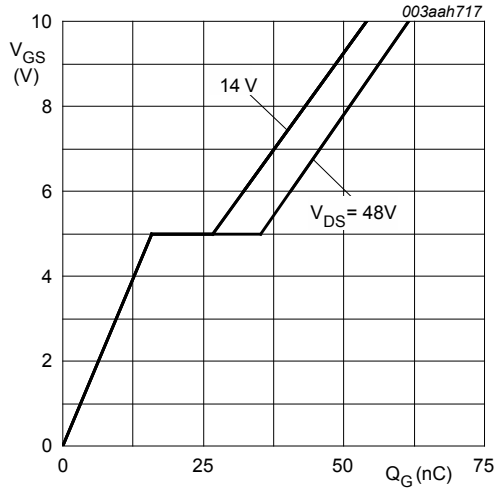

Fig. 14. Gate-source voltage as a function of gate charge; typical values

$T_j = 25°C;\ I_D = 25A$

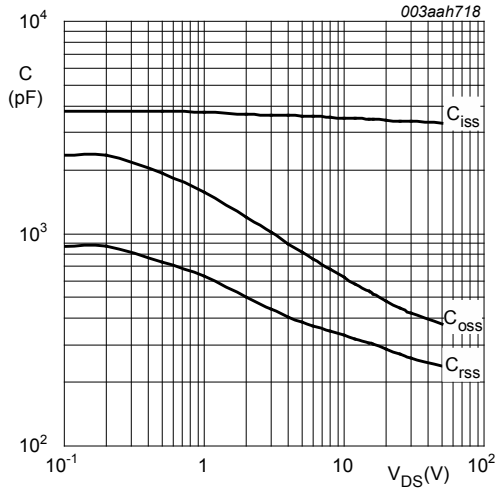

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V;\ f = 1MHz$

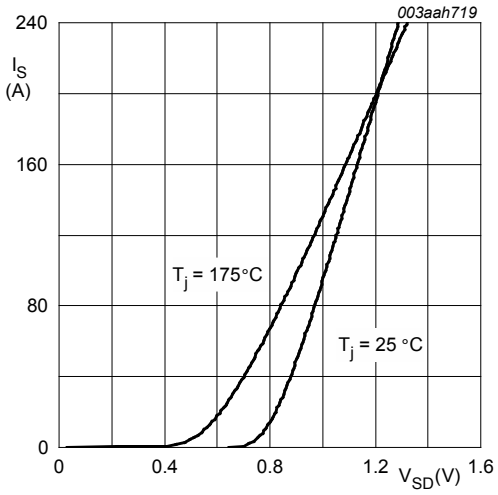

Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

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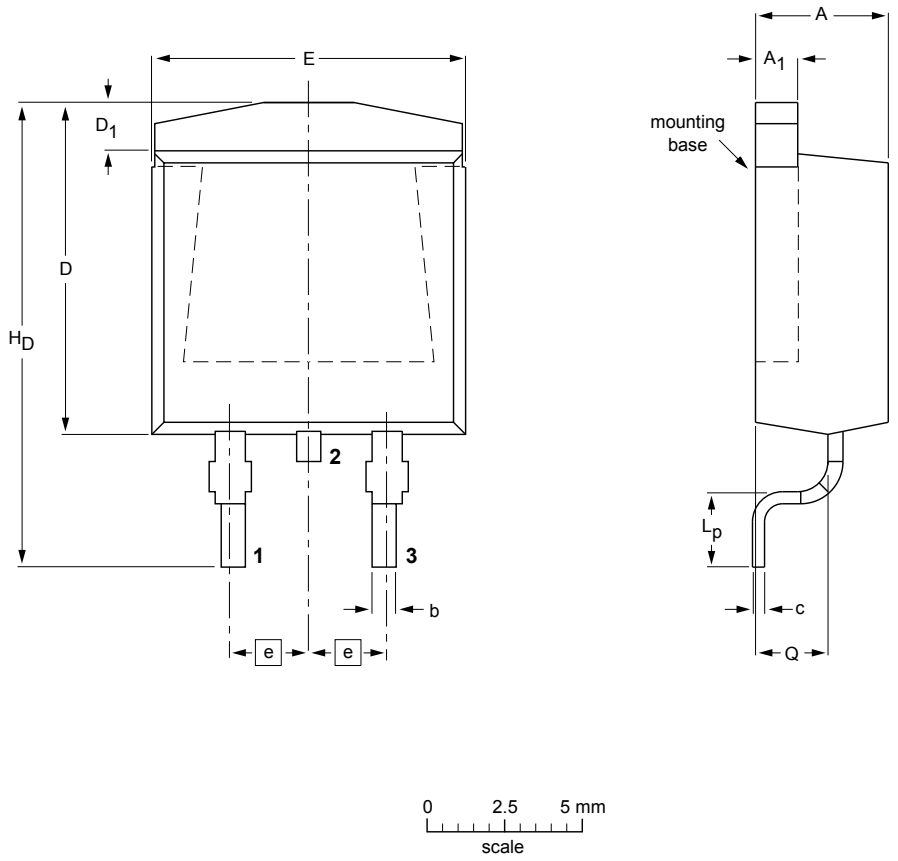
7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) **SOT404**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D max.	D_1	E	e	L_p	H_D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						~~05-02-11~~ 06-03-16

Fig. 17. D2PAK (SOT404)

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8.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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9. Contents

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